

PATENT ABSTRACTS OF JAPAN

B14

(11)Publication number : 61-210623
(43)Date of publication of application : 18.09.1986

(51)Int.CI. H01L 21/205
H01L 29/80

(21)Application number : 60-052974 (71)Applicant : SONY CORP
(22)Date of filing : 15.03.1985 (72)Inventor : ISHIBASHI AKIRA
MORI YOSHIFUMI

(54) MANUFACTURE OF SEMICONDUCTOR DEVICE

(57)Abstract:

PURPOSE: To arrange and form a lot of minute hetero interface intersecting facial direction by controlling width of an island spreading in direction of a face where the second compound semiconductor layer is deposited on the first compound semiconductor layer.

CONSTITUTION: When epitaxial growth is performed for the first compound semiconductor layer e.g. GaAs layer 2 on a substrate 1 e.g. GaAs substrate by MOCVD and is consequently performed for the second compound semiconductor layer 3 by MOCVD by changeovering supply raw gas, an island 4 of a low atomic layer is generated to the layers 2, 3. The island 4 selects the width W in the range of epitaxial growth temp. at a hetero interface of the both layers 2, 3 i.e. the substrate temp. 650W850° C at the time of MOCVD and the hetero interface of AlAs/GaAs formed to the side face of the island 4 by selecting pitch under temp. control e.g. many hetero interfaces crossing with deposited face direction of the both layers 2, 3 are formed.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]